

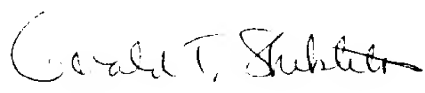
A¹
4. (amended) A silicon single crystal wafer with decreased grown-in defects, which is obtained from said silicon single crystal ingot according to Claim 1.

5. (amended) A silicon perfect single crystal wafer free from grown-in defects, which is obtained from said silicon single crystal ingot according to Claim 1.

A²
23. (amended) The CZ method-based single crystal ingot production device according to Claim 17, characterized in that said single crystal ingot is a single crystal ingot, including a portion of a perfect crystal.

Respectfully submitted,

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